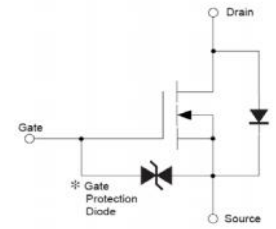




BSS84KT P-CHANNEL MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-50 V	8 Ω @-10V	-0.13A
	10 Ω @-5V	

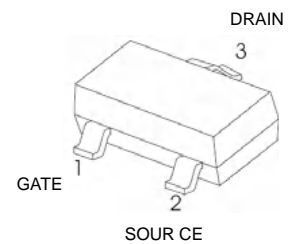


DESCRIPTION

These miniature surface mount MOSFETs reduce power loss conserve energy, making this device ideal for use in small power management circuitry.

FEATURE

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space



SOT-523

APPLICATION

- DC-DC converters, load switching, power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

MARKING : 84K

MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-0.13	A
Pulsed Drain Current (note 1) @tp <10 μs	I_{DM}	-0.52	A
Power Dissipation	P_D	225	mW
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	556	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}C$
Maximum Lead Temperature for Soldering Purposes , Duration for 5 Seconds	T_L	260	$^{\circ}C$



MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-50			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -50V, V_{GS} = 0V$			-15	μA
		$V_{DS} = -25V, V_{GS} = 0V$			-0.1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 80	μA
Gate threshold voltage (note 3)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.9		-2	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = -5V, I_D = -0.1A$			10	Ω
		$V_{GS} = -10V, I_D = -0.1A$			8	Ω
Forward transconductance (note 1)	g_{FS}	$V_{DS} = -25V; I_D = -100mA$	50			mS
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	$V_{DS} = -5V, V_{GS} = 0V, f = 1MHz$		30		pF
Output capacitance	C_{oss}			10		pF
Reverse transfer capacitance	C_{rss}			5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15V,$ $R_L = 50\Omega, I_D = -2.5A$		2.5		ns
Turn-on rise time	t_r			1		ns
Turn-off delay time	$t_{d(off)}$			16		ns
Turn-off fall time	t_f			8		ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
Continuous Current	I_S				-0.13	A
Pulsed Current	I_{SM}				-0.52	A
Diode forward voltage (note 3)	V_{SD}	$I_S = -0.13A, V_{GS} = 0V$			-2.2	V

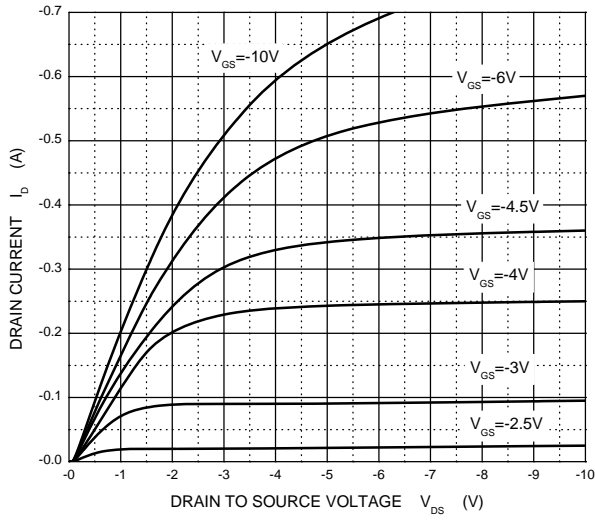
Notes :

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , $t \leq 10s$.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycles $\leq 2\%$.
4. Guaranteed by design, not subject to producing.

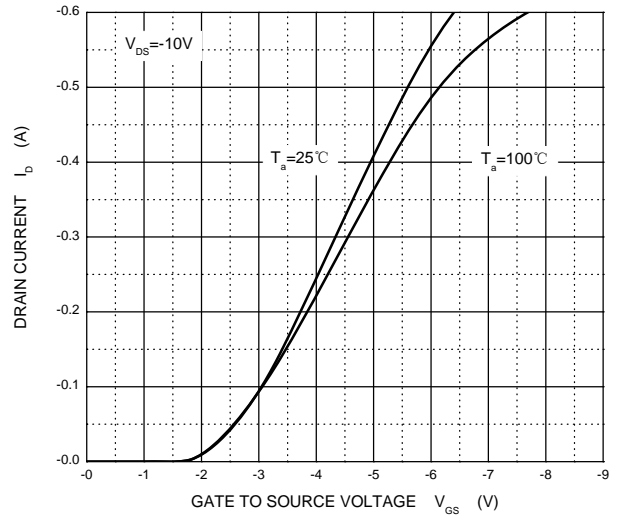


Typical Characteristics

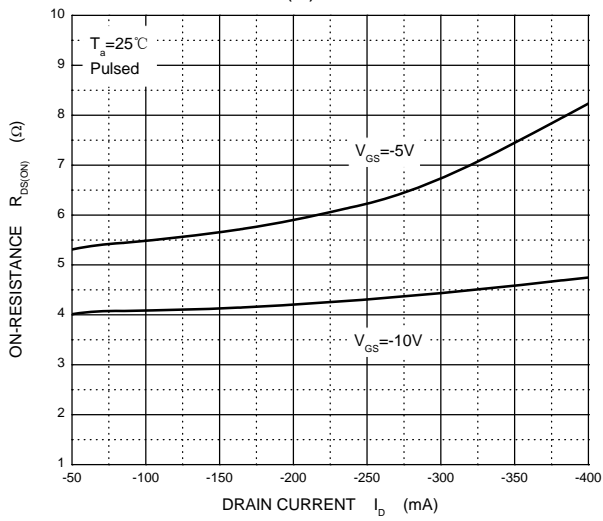
Output Characteristics



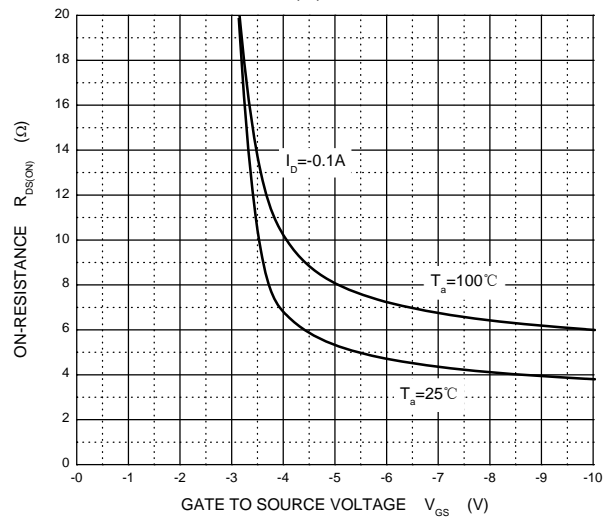
Transfer Characteristics



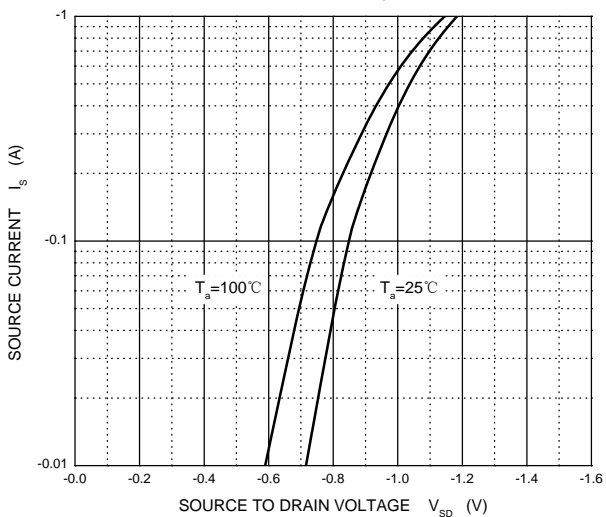
$R_{DS(ON)}$ — I_D



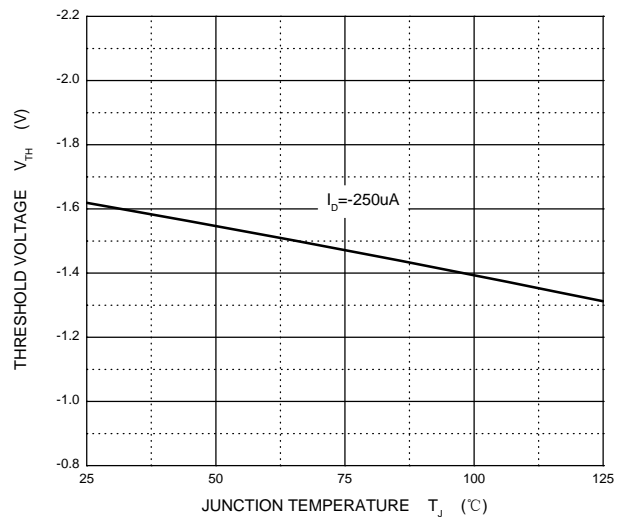
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}

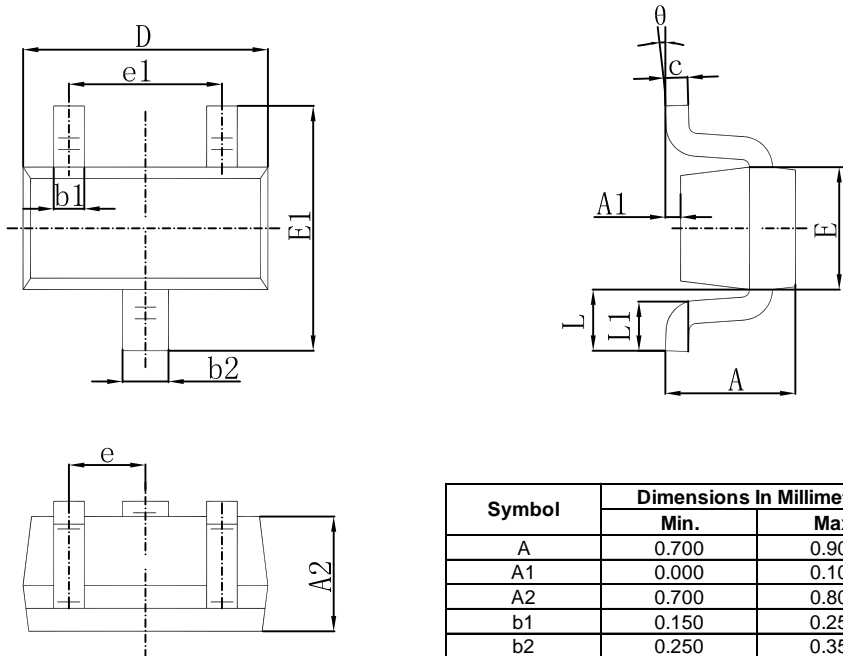


Threshold Voltage



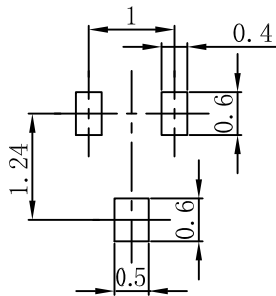


SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.